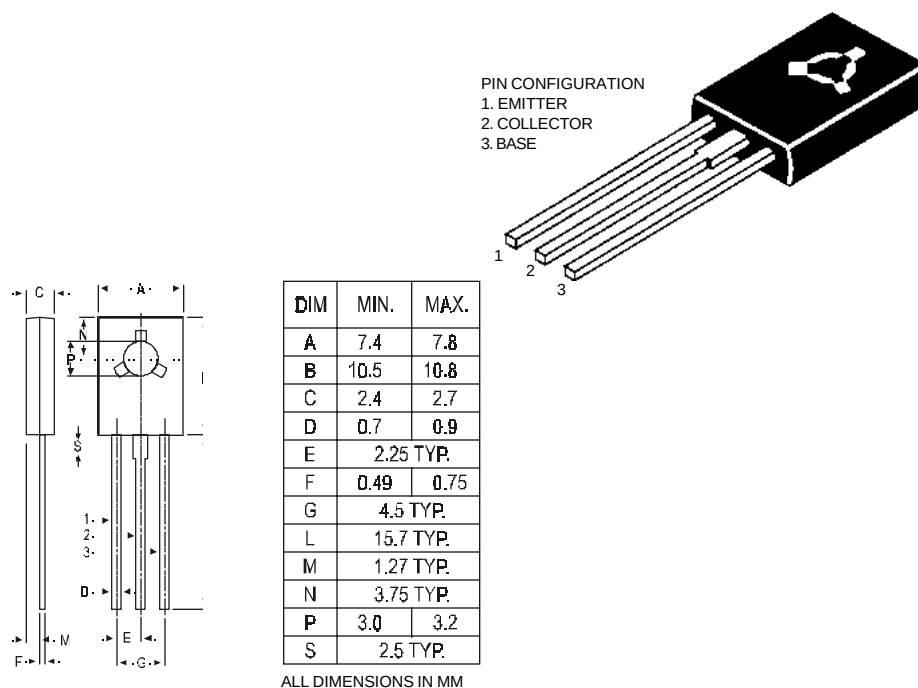


TO-126 (SOT-32) Plastic Package

**CSB631, CSB631K
CSD600, CSD600K**

*CSB631, 631K PNP PLASTIC POWER TRANSISTORS
CSD600, 600K NPN PLASTIC POWER TRANSISTORS
Low frequency Power Amplifier and Medium Speed Switching Applications*



ABSOLUTE MAXIMUM RATINGS

		631 600	631K 600K
Collector-base voltage (open emitter)	V_{CBO}	max. 100	120 V
Collector-emitter voltage (open base)	V_{CEO}	max. 100	120 V
Collector current	I_C	max. 1.0	A
Total power dissipation up to $T_C = 25^\circ\text{C}$	P_C	max. 8.0	W
Junction temperature	T_j	max. 150	$^\circ\text{C}$
Collector-emitter saturation voltage $I_C = 0.5 \text{ A}; I_B = 50 \text{ mA}$	V_{CEsat}	max. 0.4	V
D.C. current gain $I_C = 50 \text{ mA}; V_{CE} = 5 \text{ V}$	h_{FE}	min. 60 max. 320	

RATINGS (at $T_A=25^\circ\text{C}$ unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)	V_{CBO}	max. 100	120 V
Collector-emitter voltage (open base)	V_{CEO}	max. 100	120 V

**CSB631, CSB631K
CSD600, CSD600K**

		631 600	631K 600K	
Emitter-base voltage (open collector)	V_{EBO}	max.	5.0	V
Collector current	I_C	max.	1.0	A
Collector current (peak)	I_{CP}	max.	2.0	mA
Total power dissipation up to $T_A = 25^\circ\text{C}$	P_C	max.	1.0	W
Total power dissipation up to $T_C = 25^\circ\text{C}$	P_C	max.	8.0	W
Junction temperature	T_j	max.	150	$^\circ\text{C}$
Storage temperature	T_{stg}		-65 to +150	$^\circ\text{C}$

CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$ unless otherwise specified

		631 600	631K 600K	
Collector cutoff current $I_E = 0; V_{CB} = 50\text{ V}$	I_{CBO}	max.	1.0	μA
Emitter cut-off current $I_C = 0; V_{EB} = 4\text{ V}$	I_{EBO}	max.	1.0	μA
Breakdown voltages $I_C = 1\text{ mA}; I_B = 0$	V_{CEO}	min.	100	120 V
$I_C = 10\text{ }\mu\text{A}; I_E = 0$	V_{CBO}	min.	100	120 V
$I_E = 10\text{ }\mu\text{A}; I_C = 0$	V_{EBO}	min.	5.0	V
Saturation voltages $I_C = 500\text{ mA}; I_B = 50\text{ mA}$	V_{CEsat}	max.	0.4	V
	V_{BEsat}	max.	1.2	V
D.C. current gain $I_C = 50\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE}^*	min.	60	
		max.	320	
$I_C = 500\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE}	min.	20	
Transition frequency $I_C = 50\text{ mA}; V_{CE} = 10\text{ V}$	f_T	typ.	110	MHz
		typ.	130	MHz
Output capacitance $V_{CB} = 10\text{ V}; I_E = 0; f = 1\text{ MHz}$	C_{ob}	typ.	30	pF
	C_{ob}	typ.	20	pF

*** h_{FE} classification: D60 - 120, E = 100 - 200, F 160 - 320**

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/ CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



CDIL is a registered Trademark of
Continental Device India Limited

C-120 Naraina Industrial Area, New Delhi 110 028, India.
Telephone + 91-11-2579 6150, 5141 1112 Fax + 91-11-2579 5290, 5141 1119
email@cdil.com www.cdilsemi.com